



SOT-23 Plastic-Encapsulate Transistors

MMBT5401 TRANSISTOR (PNP)

FEATURES

- Complementary to MMBT5551
- Ideal for medium power amplification and switching

MARKING: 2L

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.6	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}$, $I_E = 0$	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $I_B = 0$	-150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -120\text{V}$, $I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}$, $I_C = 0$		-0.1	μA
DC current gain	h_{FE1}	$V_{CE} = -5\text{V}$, $I_C = -1\text{mA}$	80		
	h_{FE2}	$V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$	100	300	
	h_{FE3}	$V_{CE} = -5\text{V}$, $I_C = -50\text{mA}$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$		-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$ $f = 30\text{MHz}$	100		MHz

Typical Characteristics

MMBT5401

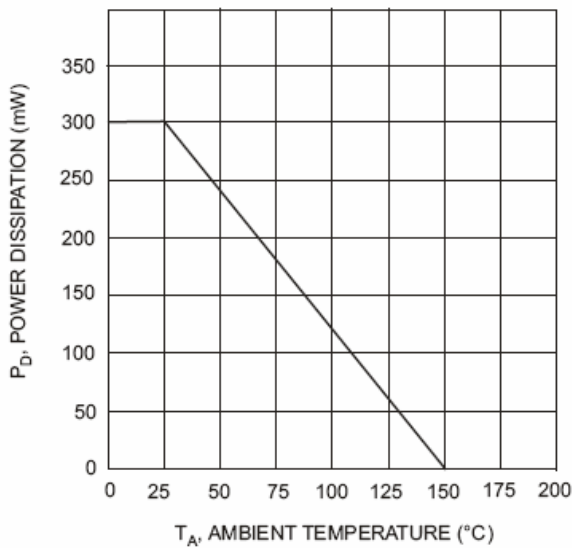


Fig. 1, Max Power Dissipation vs Ambient Temperature

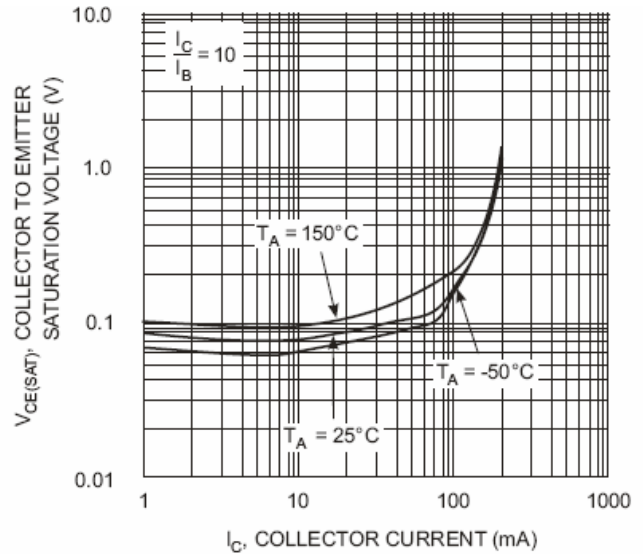


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

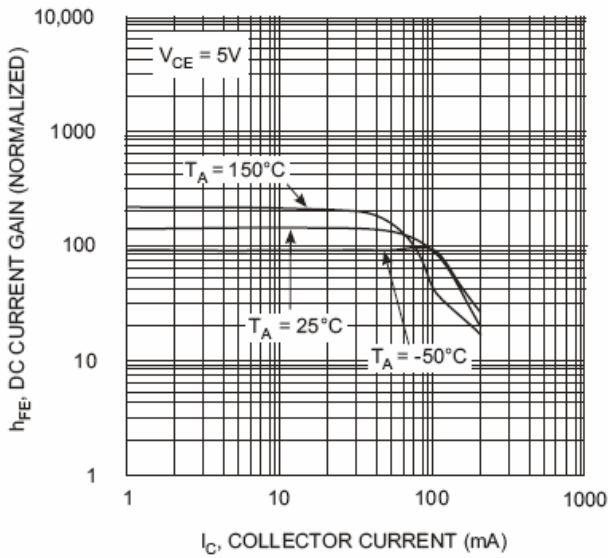


Fig. 3, DC Current Gain vs. Collector Current

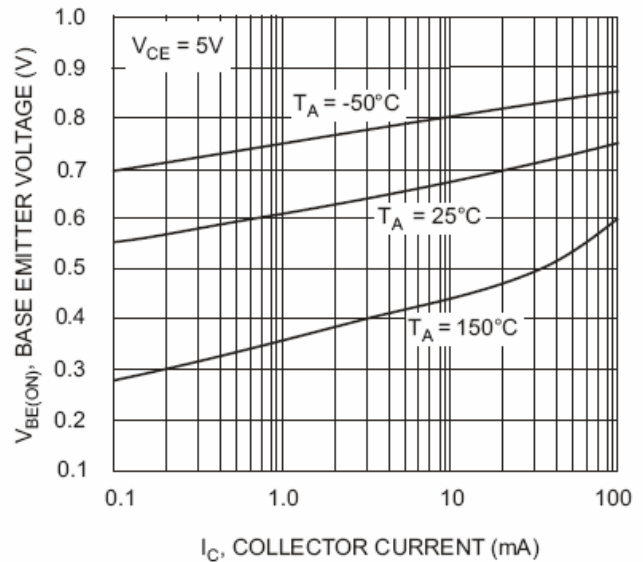


Fig. 4, Base Emitter Voltage vs. Collector Current

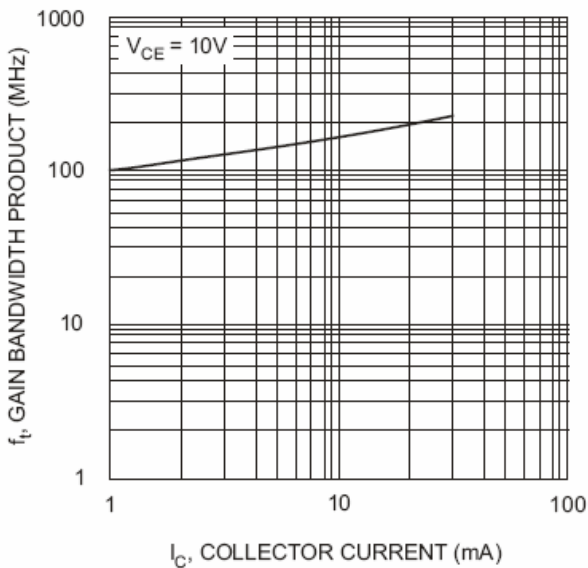


Fig. 5, Gain Bandwidth Product vs Collector Current